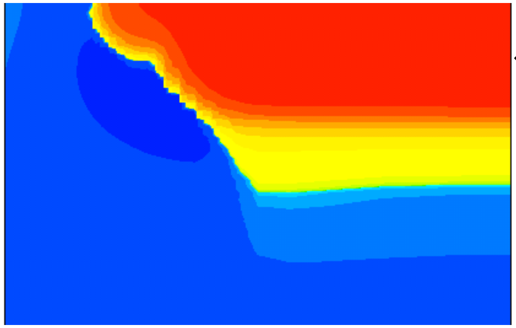
Lecture4: Diode (2)

Sung-Min Hong (smhong@gist.ac.kr)

Semiconductor Device Simulation Lab.
School of Electrical Engineering and Coumputer Science
Gwangju Institute of Science and Technology

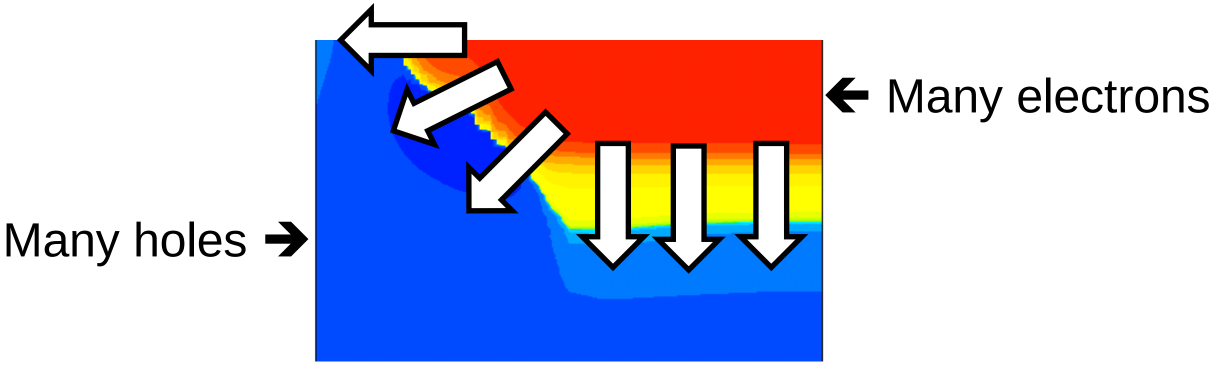
Equilibrium (1)

- When the applied voltage is zero, no current occurs.
  - Many electrons in the “red” region. (Doped with Arsenic ions. “n-type”)
  - Many holes in the “blue” region. (Doped with Boron ions. “p-type”)
  - Due to the diffusion mechanism, they tend to spread over.
  - Then, we will have the net current! (It’s not possible.)



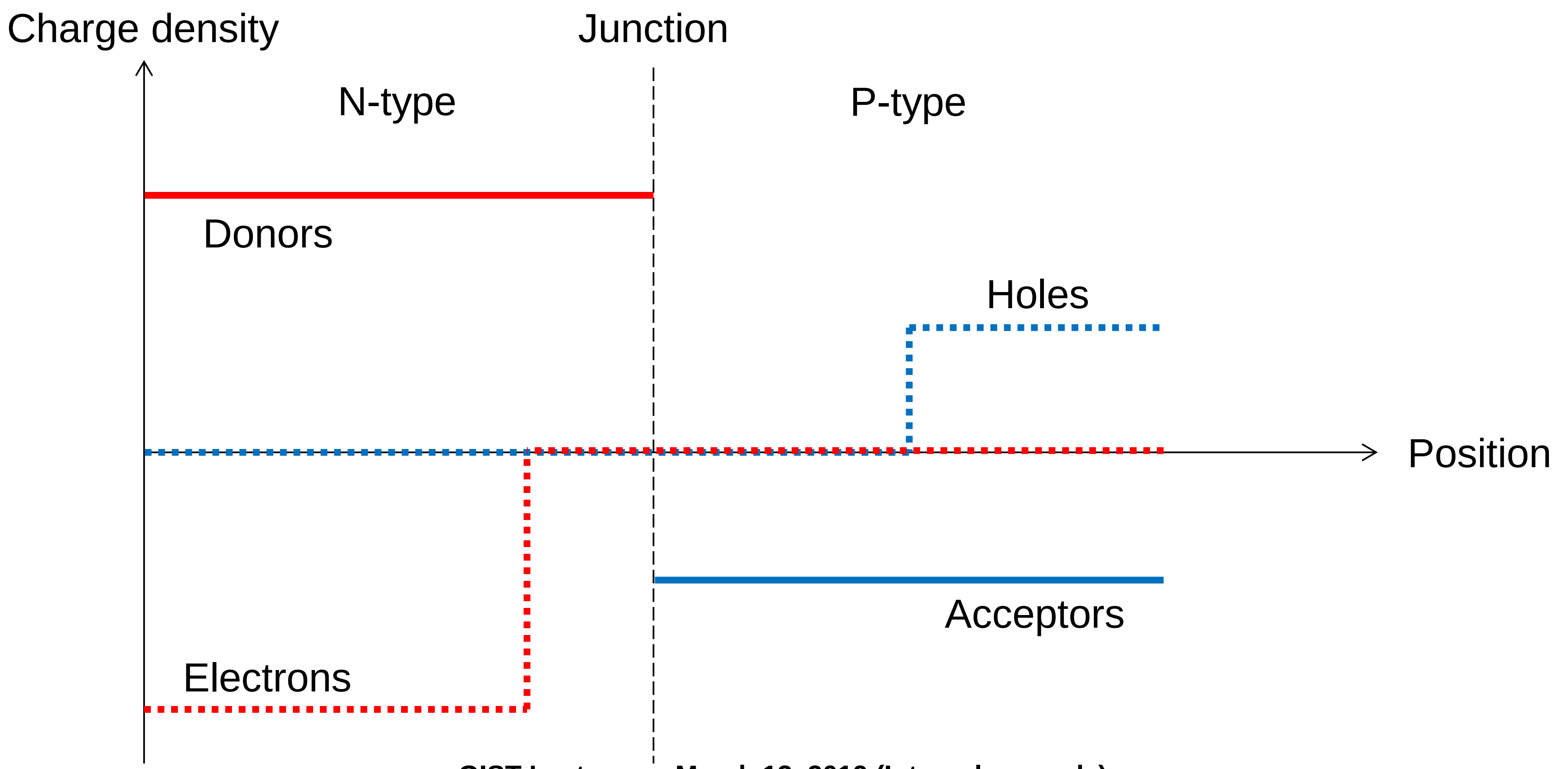
Equilibrium (2)

- An electric field is built. (Built-in field)
  - It pushes the electrons back to the n-type region.
  - It pushes the holes back to the p-type region.
  - Direction of the electric field?
  - At equilibrium, drift (due to the electric field) and diffusion (due to the density difference) are exactly matched.



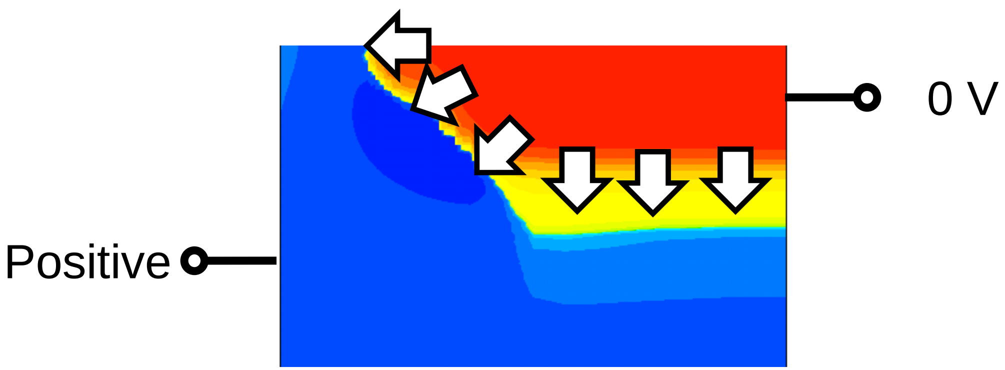
Built-in field

- How can we justify the electric field?
  – Net (+) and (-) charges due to depletion of mobile carriers



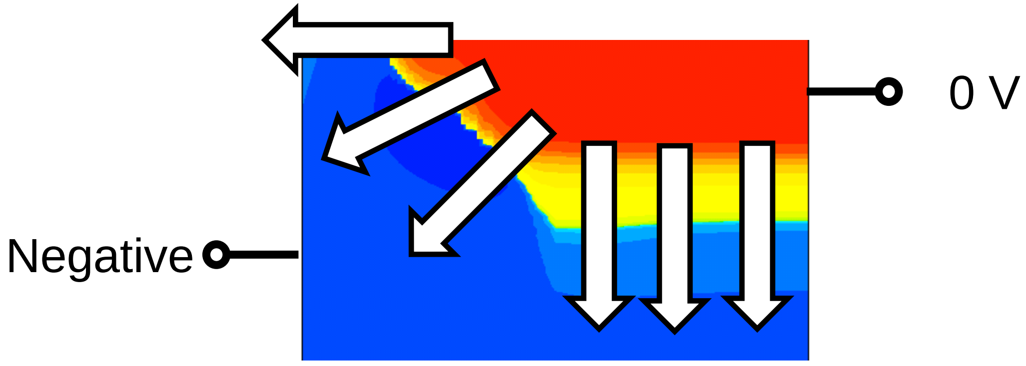
Forward bias

- We have a positive voltage at the anode.
  - Additional electric field from positive to 0 V
  - The external voltage opposes the built-in potential.
  - No sufficiently strong electric field to prevent the diffusion
  - It raises the diffusion currents substantially.



Reverse bias

- We have a negative voltage at the anode.
  - Additional electric field from 0 V to negative
  - The applied voltage enhances the field.
  - Even stronger electric field to prevent the diffusion
  - It prohibits the current flow.
- Highly nonlinear operation!



IV characteristics (1)

- Review
  - The diode current, I_D, is depedent on the diode voltage, V_D.
  - Then, what is $I_D(V_D)$?
- Compare $V_D = 0.3$ V, 0.4 V, and 0.5 V.
  - We know that the electric field for 0.5 V is weakest.
  - Of course, for 0.3 V, it is strongest.
  - Anyway, they are different by a constant voltage, 0.1 V.
  - Then, what about $I_D(0.3)$, $I_D(0.4)$, and $I_D(0.5)$?
  - Do you expect a linear dependence?

IV characteristics (2)

- Exponential dependence on V_D
  - V_D is normalized by the thermal voltage, $V_T = \frac{k_B T}{q}$.
  - At 300 K, $V_T \approx 0.02585\ \mathrm{V} = 25.85\ \mathrm{mV}$.
  - Then, the diode current can be written as

$$I_D = I_S\left(\exp\frac{V_D}{V_T} - 1\right)$$

  - Here, the “reverse saturation current” (I_S) is a given constant. It’s a small current.

IV characteristics (3)

- Some limiting cases:

$$I_D = I_S\left(\exp\frac{V_D}{V_T} - 1\right)$$

  - When V_D is close to zero, $\exp\frac{V_D}{V_T} \approx 1 + \frac{V_D}{V_T}$

$$I_D = I_S\frac{V_D}{V_T}$$

  - When V_D is negative and $V_D \ll -V_T$, $\exp\frac{V_D}{V_T} \approx 0$

$$I_D = -I_S$$

  - When V_D is positive and $V_D \gg V_T$, $I_D = I_S \exp\frac{V_D}{V_T}$

Homework#2

- Due: 09:00, March 18
  - Submit your Homework answer sheet (hardcopy) directly to Mr. Suhyeong Cha, our TA.
  - His office: EECS building C-411
- Solve following problems of the 2018 mid-term exam.
  - P8
  - P9
  - P11
- Solve following problems of the 2018 mid-term exam.
  - P10
  - P11
  - P14